



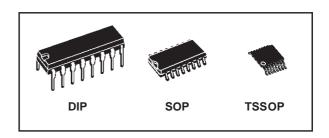
8 CHANNEL MULTIPLEXER

- HIGH SPEED:
 - t_{PD} = 17ns (TYP.) at V_{CC} = 6V
- LOW POWER DISSIPATION: $I_{CC} = 4\mu A(MAX.)$ at $T_A=25^{\circ}C$
- HIGH NOISE IMMUNITY: V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE: |I_{OH}| = I_{OL} = 4mA (MIN)
- BALANCED PROPAGATION DELAYS: t_{PLH} ≅ t_{PHL}
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 151



The M74HC151 is an high speed CMOS 8 CHANNEL MULTIPLEXER fabricated with silicon gate C^2 MOS technology.

It provides, in one package, the ability to select one bit of data from up to eight sources. The M74HC151 can be used as a universal function generator to generate any logic function of four variables. Outputs Y and W are complementary;

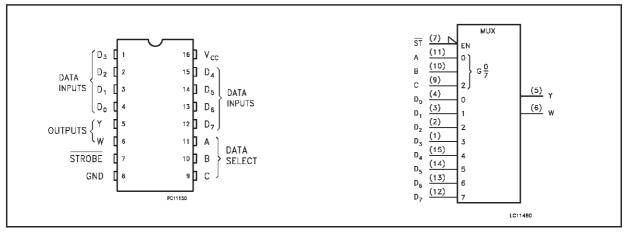


ORDER CODES

PACKAGE	TUBE	T & R
DIP	M74HC151B1R	
SOP	M74HC151M1R	M74HC151RM13TR
TSSOP		M74HC151TTR

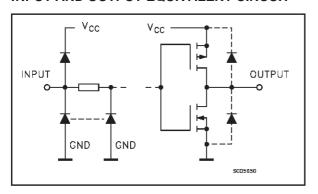
the selection depends on the address inputs A, B, and C. The strobe input must be taken low to enable this device, when the strobe is high W output is forced high and consequently Y output goes low. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



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INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

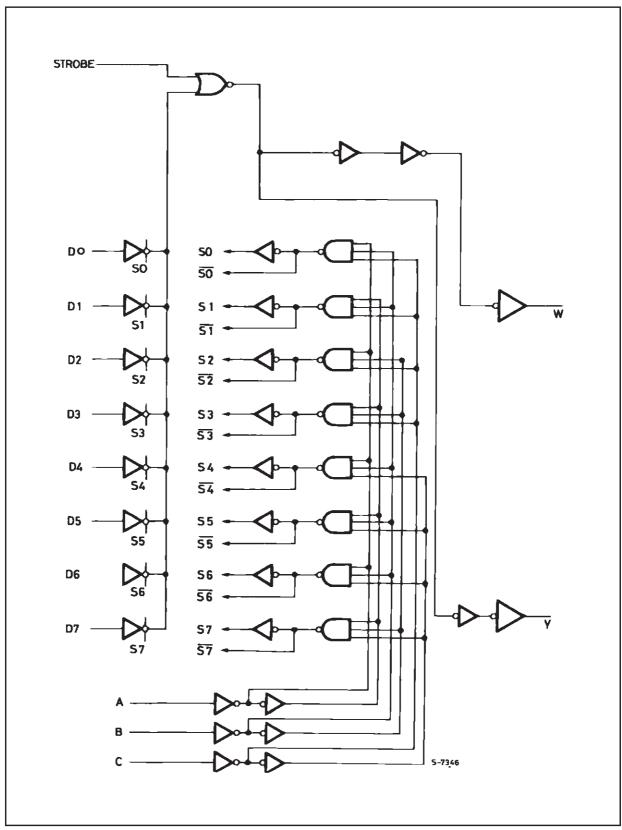
PIN No	SYMBOL	NAME AND FUNCTION
4, 3, 2, 1, 15, 14, 13, 12	D ₀ to D ₇	Multiplexer Inputs
5	Y	Multiplexer Output
6	W	Complementary Multiplexer Output
7	STROBE	Strobe Input
11, 10, 9	A, B, C	Select Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

TRUTH TABLE

	INP	UTS		OUTI	OUTPUTS		
	SELECT		STROBE	Y			
С	В	Α	s]	W		
Х	X	Х	Н	L	Н		
L	L	L	L	D ₀	\overline{D}_0		
L	L	Н	L	D ₁	D ₁		
L	Н	L	L	D ₂	\overline{D}_2		
L	Н	Н	L	D ₃	\overline{D}_3		
Н	L	L	L	D ₄	\overline{D}_4		
Н	L	Н	L	D ₅	D ₅		
Н	Н	L	L	D ₆	D ₆		
Н	Н	Н	L	D ₇	D ₇		

X : Don't Care

LOGIC DIAGRAM



This logic diagram has not be used to estimate propagation delays

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
lok	DC Output Diode Current	± 20	mA
I _O	DC Output Current	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage		2 to 6	V
VI	Input Voltage		0 to V _{CC}	V
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature		-55 to 125	°C
	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000	ns
t _r , t _f		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

DC SPECIFICATIONS

		1	Test Condition				Value				
Symbol	Parameter	V _{CC}		Т	T _A = 25°C -40 to 8			85°C	85°C -55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input	2.0		1.5			1.5		1.5		
	Voltage	4.5		3.15			3.15		3.15		V
		6.0		4.2			4.2		4.2		
V_{IL}	Low Level Input	2.0				0.5		0.5		0.5	
	Voltage	4.5				1.35		1.35		1.35	V
		6.0				1.8		1.8		1.8	
V_{OH}	High Level Output	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		
	Voltage	4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		V
		4.5	I _O =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-5.2 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	
	Voltage	4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =4.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =5.2 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μΑ
I _{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μΑ

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ns}$)

		T	est Condition				Value				
Symbol	Parameter	V _{CC}		T _A = 25°C			-40 to 85°C		-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition	2.0			30	75		95		110	
	Time	4.5			8	15		19		22	ns
		6.0			7	13		16		19	
t _{PLH} t _{PHL}	Propagation Delay	2.0			56	130		165		190	
	Time (D - W)	4.5			16	26		33		38	ns
		6.0			14	22		28		32	
t _{PLH} t _{PHL}	Propagation Delay	2.0			56	130		165		190	
	Time (D - Y)	4.5			16	26		33		38	ns
		6.0			14	22		28		32	
t _{PLH} t _{PHL}	Propagation Delay	2.0			30	85		105		125	
	Time (STROBE-W)	4.5			10	17		21		25	ns
		6.0			9	14		18		21	
t _{PLH} t _{PHL}	Propagation Delay	2.0			30	85		105		125	
	Time (STROBE-Y)	4.5			10	17		21		25	ns
		6.0			9	14		18		21	
t _{PLH} t _{PHL}	Propagation Delay	2.0			72	160		200		235	
	Time (A, B, C - W)	4.5			20	32		40		47	ns
		6.0			17	27		34		40	
t _{PLH} t _{PHL}	Propagation Delay	2.0			72	160		200		235	
	Time (A, B, C - Y)	4.5			20	32		40		47	ns
		6.0			17	27		34		40	

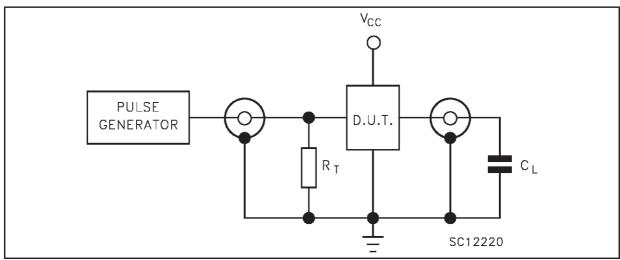
CAPACITIVE CHARACTERISTICS

			Test Condition		Value						
Symbol	Parameter	V _{CC}		T	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C _{IN}	Input Capacitance	5.0			5	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0			63						pF

¹⁾ C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

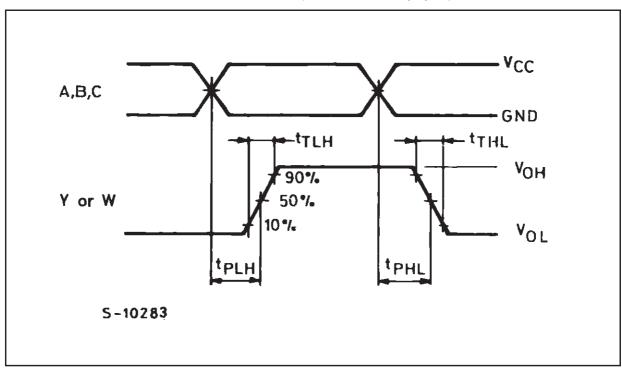
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TEST CIRCUIT

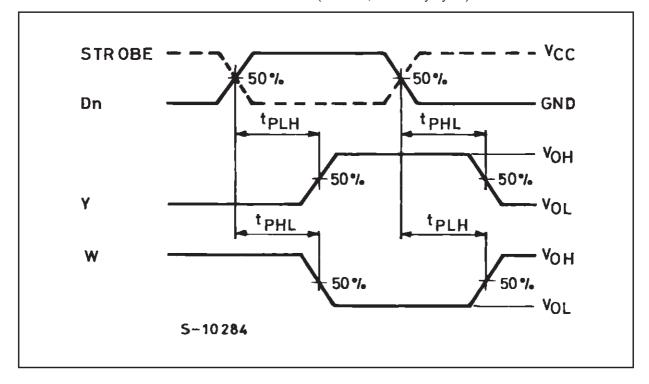


 C_L = 50pF or equivalent (includes jig and probe capacitance) R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM 1: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)

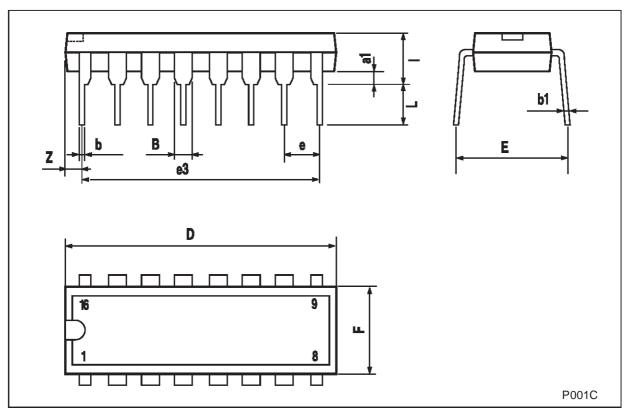


WAVEFORM 2: PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



Plastic DIP-16 (0.25) MECHANICAL DATA

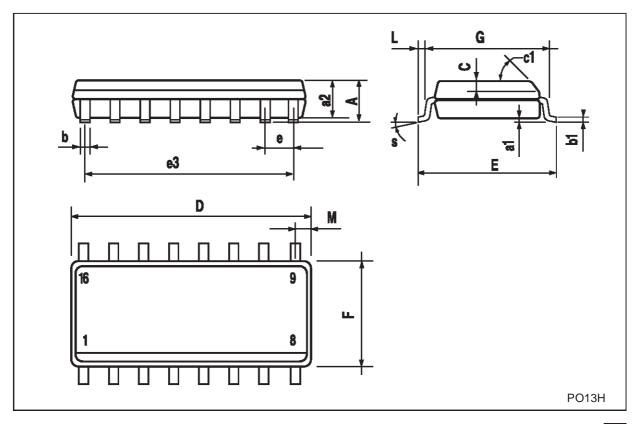
DIM.		mm.			inch	
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



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SO-16 MECHANICAL DATA

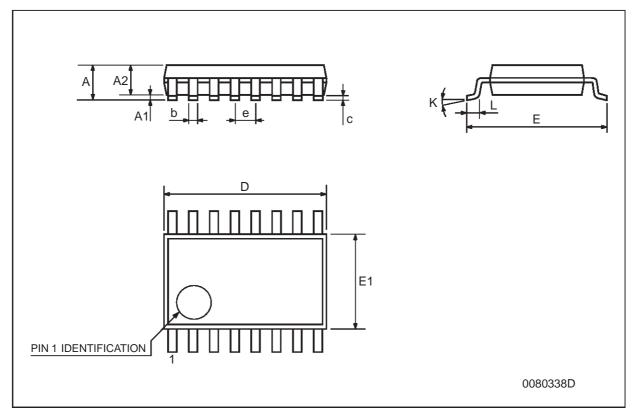
DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
еЗ		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (r	max.)	•	



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TSSOP16 MECHANICAL DATA

DIM.		mm.		inch				
DIWI.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			1.2			0.047		
A1	0.05		0.15	0.002	0.004	0.006		
A2	0.8	1	1.05	0.031	0.039	0.041		
b	0.19		0.30	0.007		0.012		
С	0.09		0.20	0.004		0.0089		
D	4.9	5	5.1	0.193	0.197	0.201		
E	6.2	6.4	6.6	0.244	0.252	0.260		
E1	4.3	4.4	4.48	0.169	0.173	0.176		
е		0.65 BSC			0.0256 BSC			
К	0°		8°	0°		8°		
L	0.45	0.60	0.75	0.018	0.024	0.030		



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